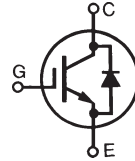
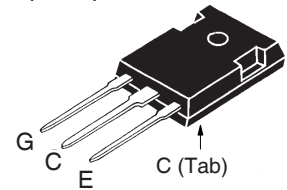


**GenX3™ 1400V IGBTs  
w/ Diode**
**IXGH20N140C3H1  
IXGT20N140C3H1**
**High-Speed PT IGBTs  
for 20 - 50 kHz Switching**


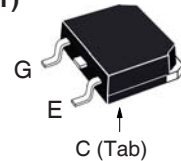
$$\begin{aligned}
 V_{CES} &= 1400V \\
 I_{C100} &= 20A \\
 V_{CE(sat)} &\leq 5.0V \\
 t_{fi(typ)} &= 32ns
 \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1400	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GE} = 1M\Omega$	1400	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	42	A
$I_{C100}$	$T_C = 100^\circ\text{C}$	20	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1ms	108	A
$I_A$	$T_C = 25^\circ\text{C}$	20	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	400	mJ
<b>SSOA (RBSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ\text{C}$ , $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 40$ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	250	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10 seconds	260	$^\circ\text{C}$
$M_d$	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-247	6	g
	TO-268	4	g

TO-247 (IXGH)



TO-268 (IXGT)



G = Gate      C = Collector  
 E = Emitter    Tab = Collector

**Features**

- Optimized for Low Switching Losses
- Square RBSOA
- High Avalanche Capability
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$ , Note 1			100 $\mu\text{A}$ 2.0 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = I_{C100}$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ\text{C}$	4.0	3.5	5.0 V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = I_{C100}, V_{CE} = 10\text{V}$ , Note 1	10	17	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1790	pF
$C_{oes}$			145	pF
$C_{res}$			50	pF
$Q_g$	$I_C = I_{C100}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		88	nC
$Q_{ge}$			18	nC
$Q_{gc}$			30	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C100}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		19	ns
$t_{ri}$			12	ns
$E_{on}$			1.35	mJ
$t_{d(off)}$			110	ns
$t_{fi}$			32	ns
$E_{off}$		0.44	0.80	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C100}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		22	ns
$t_{ri}$			13	ns
$E_{on}$			2.33	mJ
$t_{d(off)}$			144	ns
$t_{fi}$			380	ns
$E_{off}$		1.64	mJ	
$R_{thJC}$			0.50	$^\circ\text{C/W}$
$R_{thCK}$	TO-247		0.21	$^\circ\text{C/W}$

### Reverse Diode (FRED)

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 20\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 125^\circ\text{C}$		2.8	3.0 V
$I_{RM}$	$I_F = 20\text{A}, V_{GE} = 0\text{V}$ , $-di_F/dt = 750\text{A}/\mu\text{s}, V_R = 800\text{V}$		19	A
$t_{rr}$			70	ns
$R_{thJC}$			0.9	$^\circ\text{C/W}$

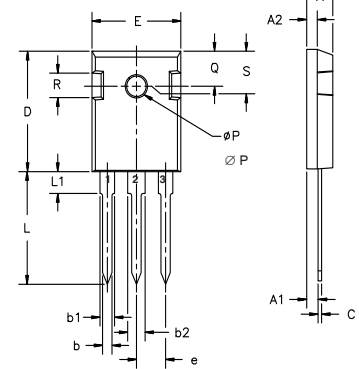
### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{Clamp})$ ,  $T_J$  or  $R_G$ .

### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

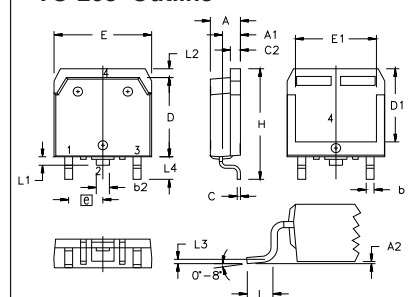
### TO-247 Outline



Terminals: 1 - Gate 2 - Collector  
3 - Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

### TO-268 Outline



Terminals: 1 - Gate 2 & 4 - Collector  
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e		.215 BSC		5.45 BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3		.010 BSC		0.25 BSC
L4	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	



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